

Automotive-grade dual N-channel 30 V, 5.9 mΩ typ., 20 A STripFET™ H5 Power MOSFET in a PowerFLAT™ 5x6 double island package

Datasheet - production data

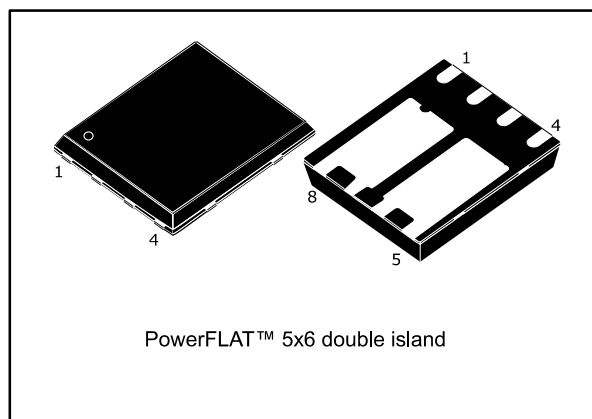
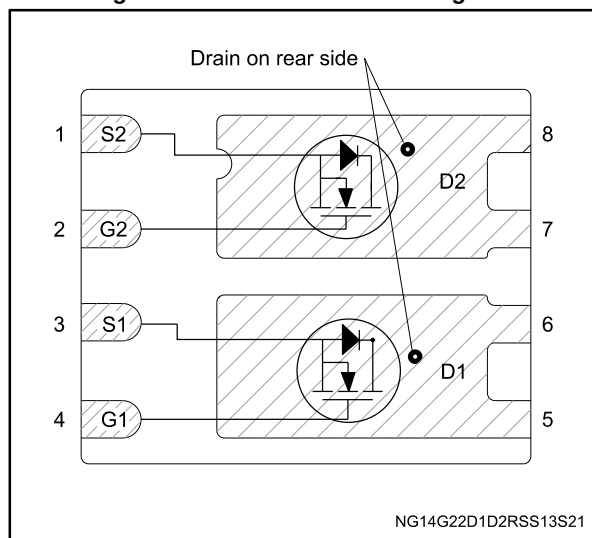


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}
STL66DN3LLH5	30 V	6.5 mΩ	20 A	4.7 W

- Designed for automotive applications and AEC-Q101 qualified
- Logic level V_{GS(th)}
- 175 °C maximum junction temperature
- Wettable flanks package

Applications

- Switching applications

Description

This device is a dual N-channel Power MOSFET developed using STMicroelectronics' STripFET™ H5 technology. The device has been optimized to achieve very low on-state resistance, contributing to a FoM that is among the best in its class.

Table 1: Device summary

Order code	Marking	Package	Packing
STL66DN3LLH5	66DN3LH5	PowerFLAT™ 5x6 double island	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	30	V
V_{GS}	Gate-source voltage	± 22	V
$I_D^{(1)}$	Drain current (continuous) at $T_{case} = 25\text{ }^{\circ}\text{C}$	78.5	A
	Drain current (continuous) at $T_{case} = 100\text{ }^{\circ}\text{C}$	55.5	
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^{\circ}\text{C}$	20	A
	Drain current (continuous) at $T_{pcb} = 100\text{ }^{\circ}\text{C}$	14.2	
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	80	A
P_{TOT}	Total dissipation at $T_{case} = 25\text{ }^{\circ}\text{C}$	72	W
$P_{TOT}^{(1)}$	Total dissipation at $T_{pcb} = 25\text{ }^{\circ}\text{C}$	4.7	
T_{stg}	Storage temperature	-55 to 175	$^{\circ}\text{C}$
T_j	Operating junction temperature		

Notes:

(1) This value is rated according to R_{thj-c}

(2) When mounted on a 1-inch² FR-4, 2 Oz copper board, $t < 10\text{ s}$.

(3) Pulse width is limited by safe operating area.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	2.08	$^{\circ}\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	32	

Notes:

(1) When mounted on a 1-inch² FR-4, 2 Oz copper board, $t < 10\text{ s}$.

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AV}	Avalanche current, not repetitive	18.5	A
$E_{AS}^{(1)}$	Single pulse avalanche energy	270	mJ

Notes:

(1) starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = 38\text{ A}$, $V_{DD} = 24\text{ V}$.

2 Electrical characteristics

($T_{\text{case}} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 5: Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$, $I_{\text{D}} = 250\text{ }\mu\text{A}$	30			V
I_{DSS}	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 30\text{ V}$			1	μA
		$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 30\text{ V}$, $T_{\text{C}} = 125\text{ }^{\circ}\text{C}$			100	
I_{GSS}	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$, $V_{\text{GS}} = \pm 22\text{ V}$			± 10	μA
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_{\text{D}} = 250\text{ }\mu\text{A}$	1		3	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$, $I_{\text{D}} = 10\text{ A}$		5.9	6.5	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5\text{ V}$, $I_{\text{D}} = 10\text{ A}$		7.1	7.9	

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{\text{DS}} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{\text{GS}} = 0\text{ V}$	-	1500	-	pF
C_{oss}	Output capacitance		-	230	-	
C_{rss}	Reverse transfer capacitance		-	23	-	
Q_{g}	Total gate charge	$V_{\text{DD}} = 15\text{ V}$, $I_{\text{D}} = 19\text{ A}$, $V_{\text{GS}} = 4.5\text{ V}$ (see Figure 14: "Test circuit for gate charge behavior")	-	12	-	nC
Q_{gs}	Gate-source charge		-	5	-	
Q_{gd}	Gate-drain charge		-	4.4	-	

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d(on)}}$	Turn-on delay time	$V_{\text{DD}} = 15\text{ V}$, $I_{\text{D}} = 9.5\text{ A}$ $R_{\text{G}} = 4.7\text{ }\Omega$, $V_{\text{GS}} = 10\text{ V}$ (see Figure 13: "Test circuit for resistive load switching times" and Figure 18: "Switching time waveform")	-	8.8	-	ns
t_{r}	Rise time		-	18	-	
$t_{\text{d(off)}}$	Turn-off delay time		-	26	-	
t_{f}	Fall time		-	4	-	

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		20	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		80	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 19\text{ A}$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 19\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 25\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 15: "Test circuit for inductive load switching and diode recovery times")	-	24		ns
Q_{rr}	Reverse recovery charge		-	12		nC
I_{RRM}	Reverse recovery current		-	1.8		A

Notes:

⁽¹⁾ Pulse width is limited by safe operating area.

⁽²⁾ Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

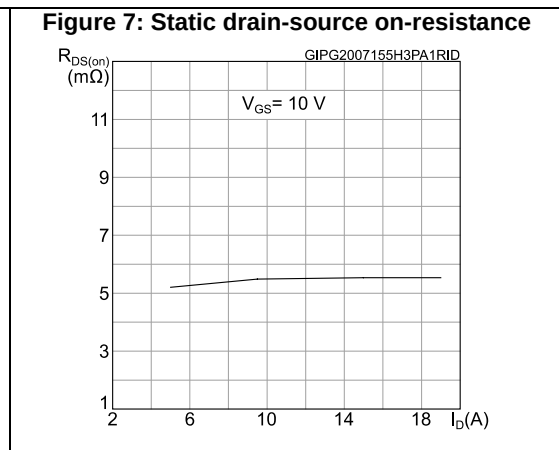
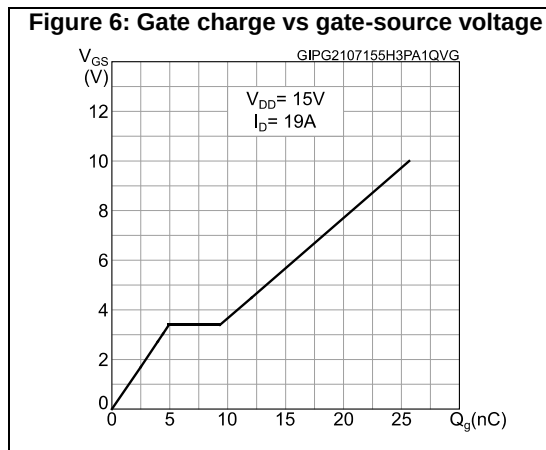
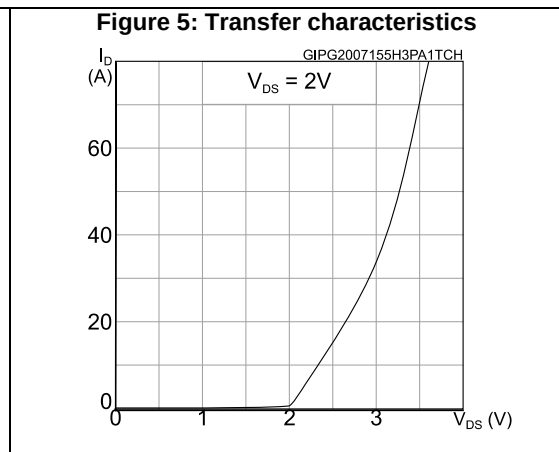
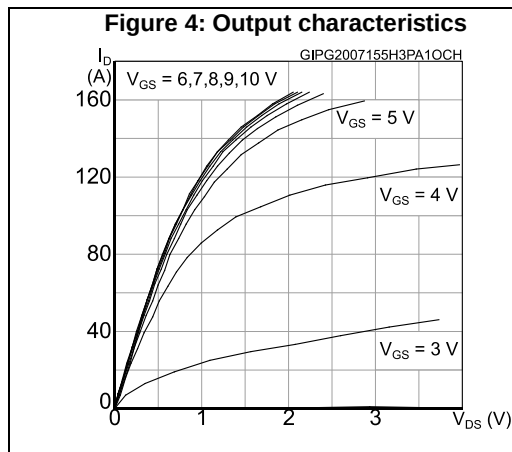
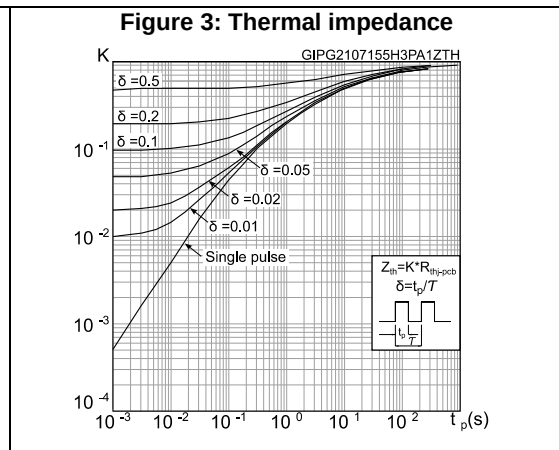
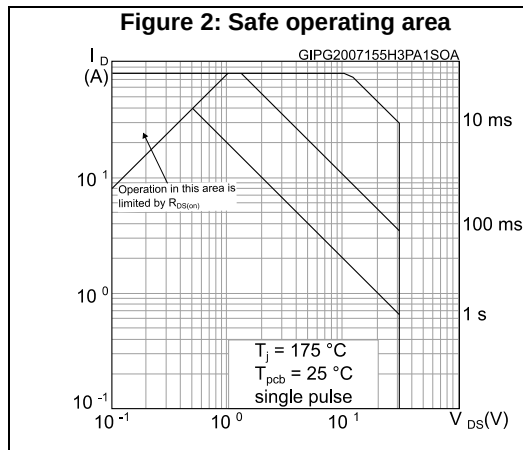


Figure 8: Capacitance variations

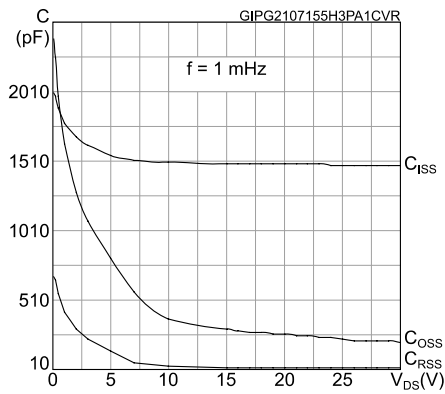


Figure 9: Normalized gate threshold voltage vs temperature

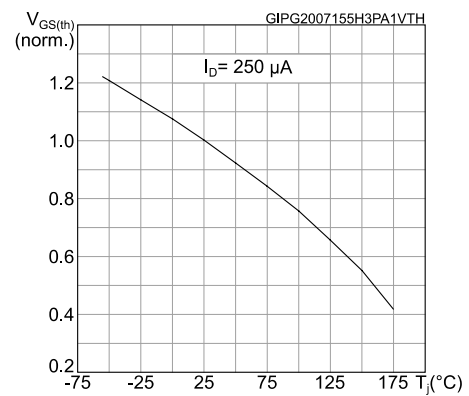


Figure 10: Normalized on-resistance vs temperature

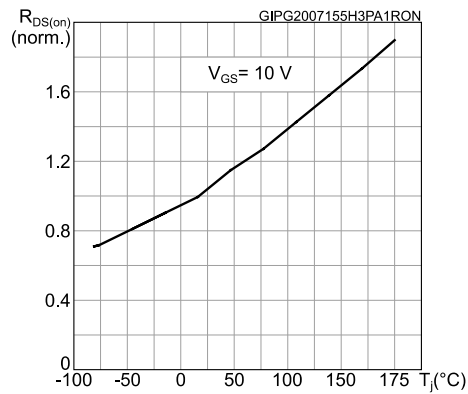


Figure 11: Normalized V(BR)DSS vs temperature

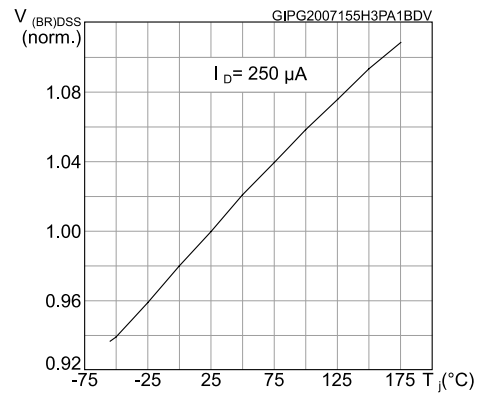
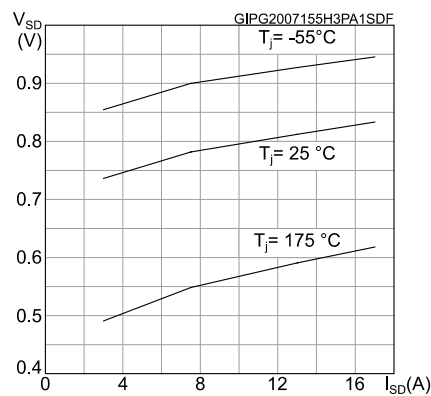
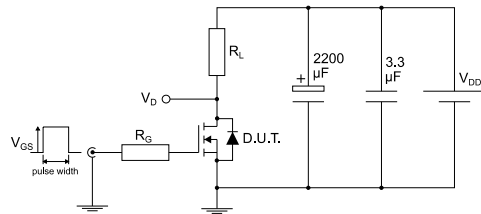


Figure 12: Source-drain diode forward characteristics



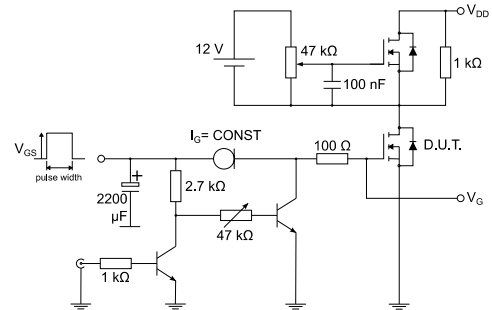
3 Test circuits

Figure 13: Test circuit for resistive load switching times



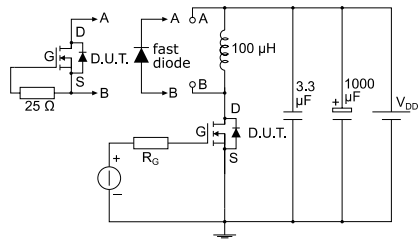
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Figure 14: Test circuit for gate charge behavior



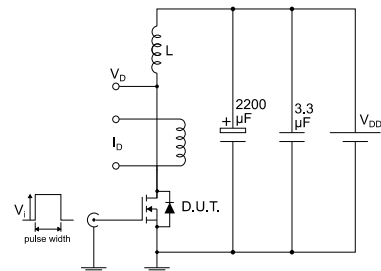
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Figure 15: Test circuit for inductive load switching and diode recovery times



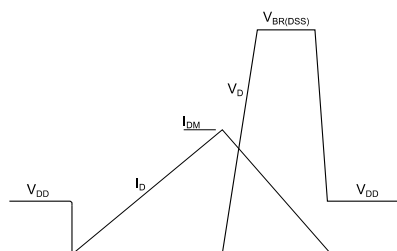
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Figure 16: Unclamped inductive load test circuit



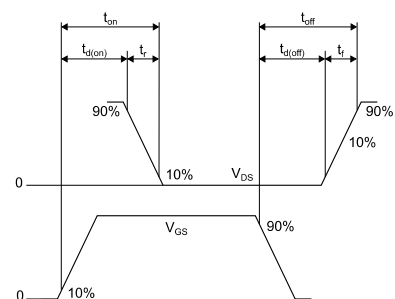
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Figure 17: Unclamped inductive waveform



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Figure 18: Switching time waveform



AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 PowerFLAT™ 5x6 double island WF type C package information

Figure 19: PowerFLAT™ 5x6 double island WF type C package outline

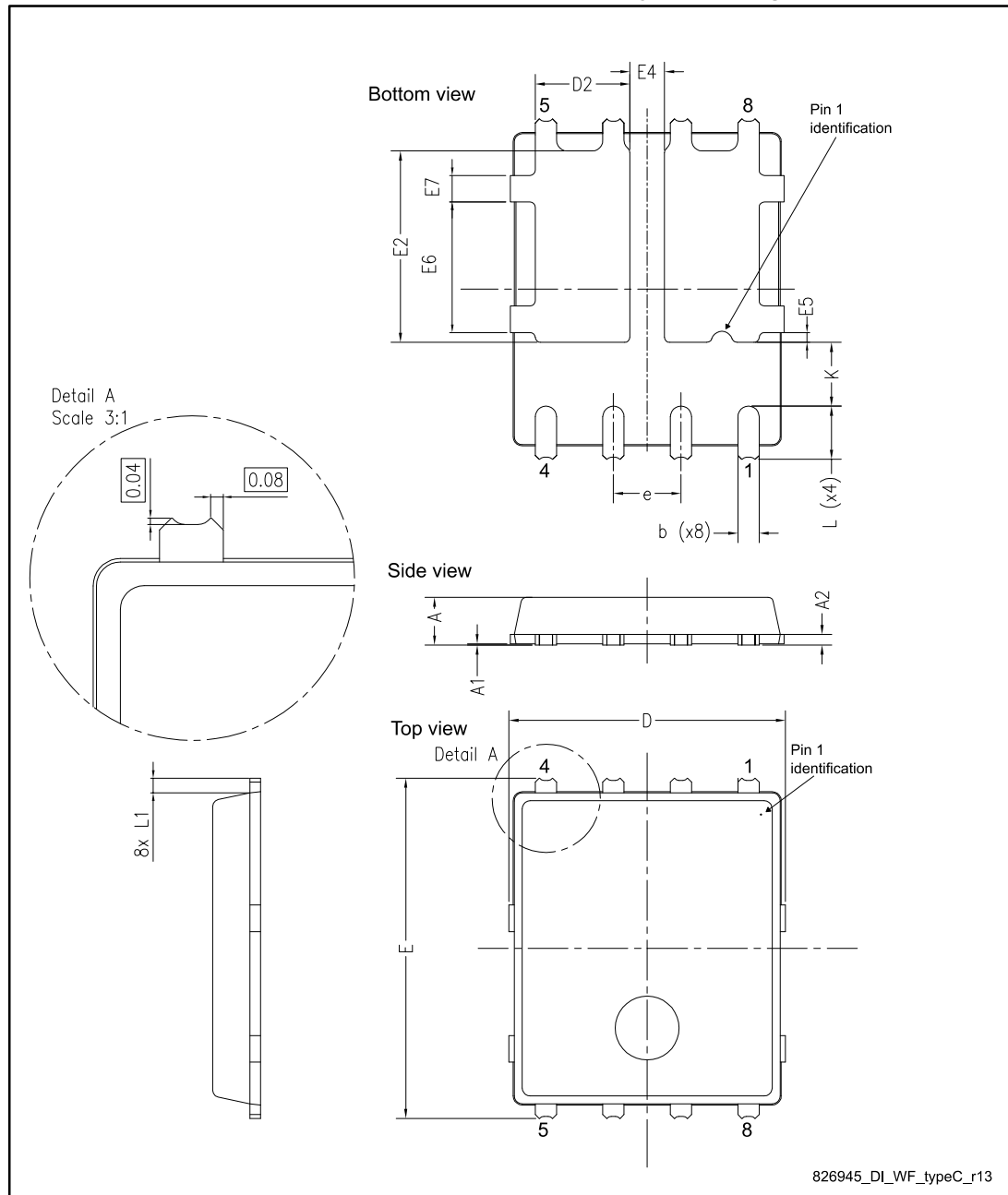
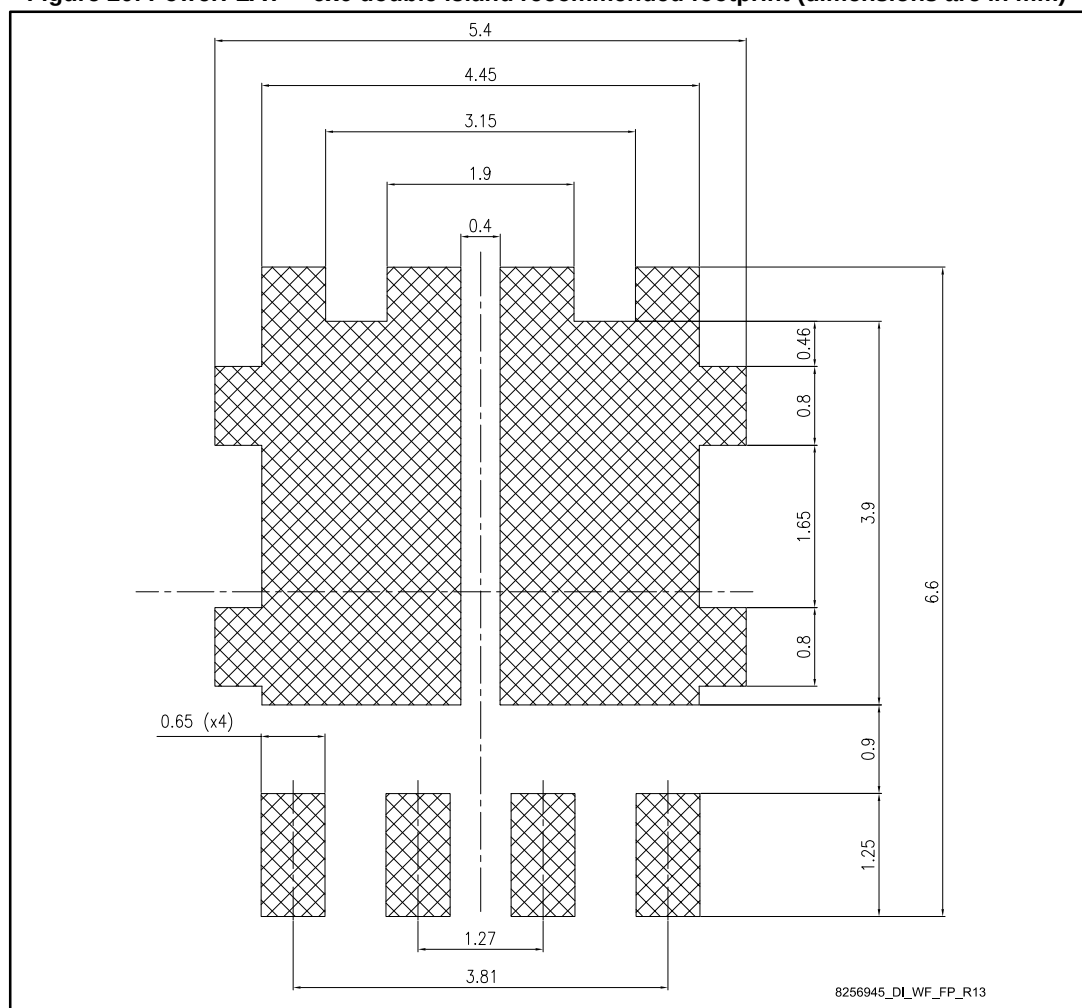


Table 9: PowerFLAT™ 5x6 double island WF type C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D	5.00	5.20	5.40
D2	1.68		1.88
E	6.20	6.40	6.60
E2	3.50		3.70
E4	0.55		0.75
E5	0.08		0.28
E6	2.35		2.55
E7	0.40		0.60
e		1.27	
L	0.90		1.10
L1		0.275	
K	1.05		1.35

Figure 20: PowerFLAT™ 5x6 double island recommended footprint (dimensions are in mm)



4.2 PowerFLAT™ 5x6 WF packing information

Figure 21: PowerFLAT™ 5x6 WF tape

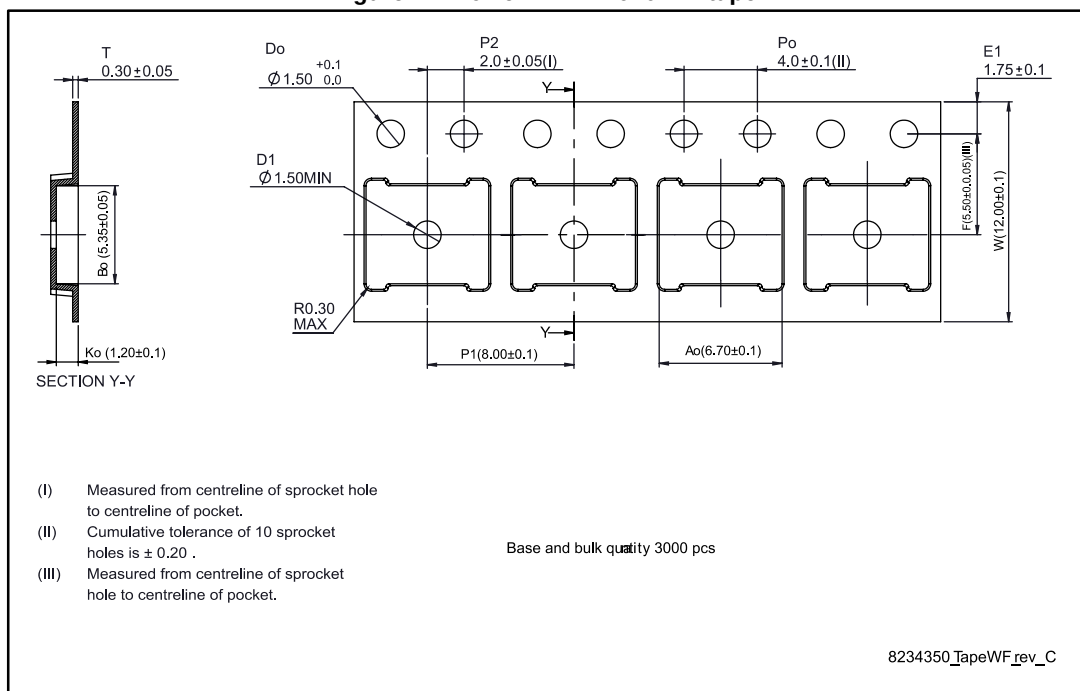


Figure 22: PowerFLAT™ 5x6 package orientation in carrier tape

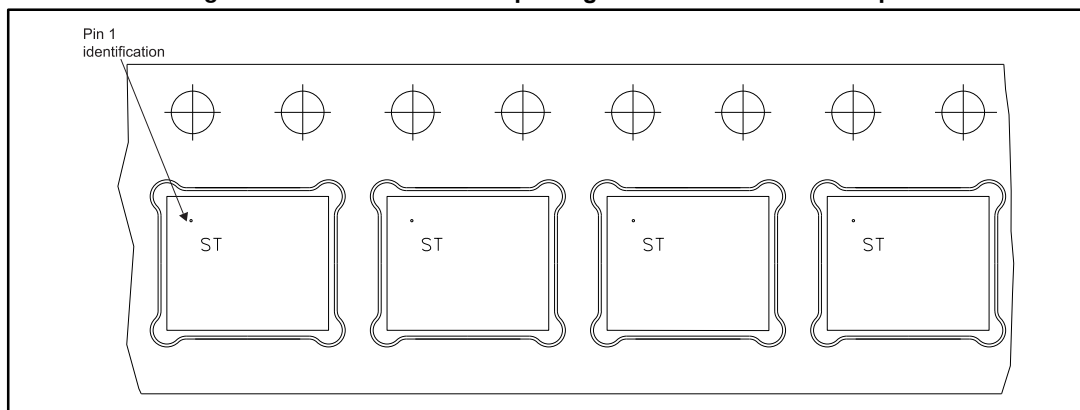
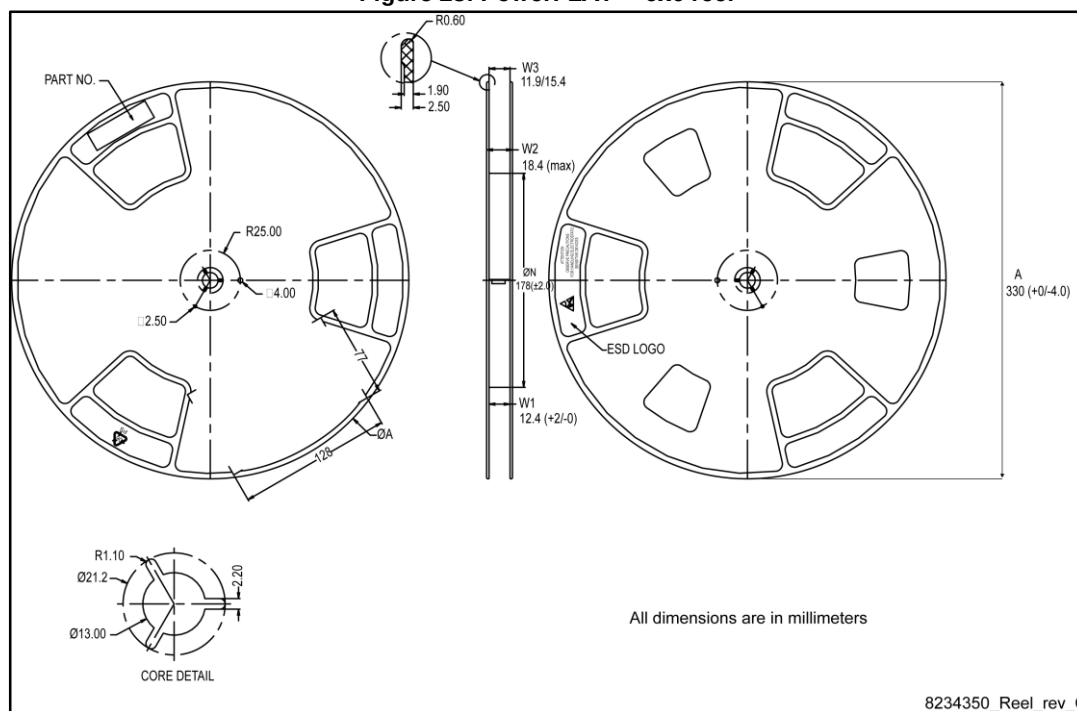


Figure 23: PowerFLAT™ 5x6 reel



5 Revision history

Table 10: Document revision history

Date	Revision	Changes
12-Oct-2011	1	First release.
14-Mar-2012	2	Document status changed from preliminary data to production data. Inserted Section 5: Packaging mechanical data. Minor text changes.
28-Aug-2015	3	Text and formatting changes throughout document Updated device marking information. Updated device package information.

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